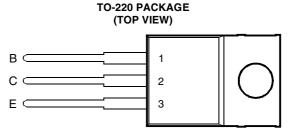
BOURNS®

- Designed for Complementary Use with TIP125, TIP126 and TIP127
- 65 W at 25°C Case Temperature
- 5 A Continuous Collector Current
- Minimum h_{FE} of 1000 at 3 V, 3 A

This series is obsolete and not recommended for new designs.



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
	TIP120		60	
Collector-base voltage (I _E = 0)	TIP121	V _{CBO}	80	V
	TIP122		100	
	TIP120		60	
Collector-emitter voltage (I _B = 0)	TIP121	VCEO	80	V
	TIP122		100	
Emitter-base voltage		V _{EBO}	5	V
Continuous collector current		I _C	5	Α
Peak collector current (see Note 1)		I _{CM}	8	Α
Continuous base current	I _B	0.1	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 2)			65	W
Continuous device dissipation at (or below) 25°C free air temperature (see Note 3)			2	W
Unclamped inductive load energy (see Note 4)			50	mJ
Operating junction temperature range			-65 to +150	°C
Storage temperature range		T _{stg}	-65 to +150	°C
Lead temperature 3.2 mm from case for 10 seconds			260	°C

- NOTES: 1. This value applies for $t_p \leq 0.3$ ms, duty cycle $\leq 10\%.$
 - 2. Derate linearly to 150°C case temperature at the rate of 0.52 W/°C.
 - 3. Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.
 - 4. This rating is based on the capability of the transistor to operate safely in a circuit of: L = 20 mH, $I_{B(on)}$ = 5 mA, R_{BE} = 100 Ω , $V_{BE(off)}$ = 0, R_S = 0.1 Ω , V_{CC} = 20 V.

TIP120, TIP121, TIP122 NPN SILICON POWER DARLINGTONS



electrical characteristics at 25°C case temperatur e

PARAMETER			TEST CONDITI	ONS	MIN TYP MA			UNIT
V _{(BR)CEO} Collector-emitter breakdown voltage	Collector-emitter			TIP120	60			
	$I_C = 30 \text{ mA}$	$I_B = 0$	TIP121	80			V	
	breakdown voltage	(see Note 5)		TIP122	100			
Collector-emitter cut-off current	Collector-emitter	V _{CE} = 30 V	I _B = 0	TIP120			0.5	
		V _{CE} = 40 V	$I_B = 0$	TIP121			0.5	mA
	cut-on current	$V_{CE} = 50 \text{ V}$	$I_B = 0$	TIP122			0.5	
Collector cut-off current	Collector cut-off	V _{CB} = 60 V	I _E = 0	TIP120			0.2	
	$V_{CB} = 80 \text{ V}$	$I_E = 0$	TIP121			0.2	mA	
	Current	V _{CB} = 100 V	$I_E = 0$	TIP122			0.2	
I _{EBO}	Emitter cut-off	V _{EB} = 5 V	I _C = 0				2	mA
iEBO	current	AER - OA					_	1117 (
h _{FE}	Forward current	$V_{CE} = 3 V$	$I_{\rm C} = 0.5 {\rm A}$	(see Notes 5 and 6)	1000			
"FE	transfer ratio	$V_{CE} = 3 V$	$I_C = 3 A$		1000			
V _{CE(sat)}	Collector-emitter	$I_B = 12 \text{ mA}$	I _C = 3 A	(see Notes 5 and 6)			2	V
	saturation voltage	$I_B = 20 \text{ mA}$	$I_C = 5 A$	(000 110100 0 and 0)			4	
V _{BE}	Base-emitter	V _{CE} = 3 V	$I_C = 3 A$	(see Notes 5 and 6)			2.5	V
	voltage	*CE = 0 *		(000 140100 0 and 0)			2.0	٧
V _{EC}	Parallel diode	I _F = 5 A	I _B = 0	(see Notes 5 and 6)			3.5	V
	forward voltage	iE - SA	'R − ∧	(000140103 5 2110 0)	13.		3.0	v

NOTES: 5. These parameters must be measured using pulse techniques, t_p = 300 μ s, duty cycle \leq 2%.

thermal characteristics

PARAM	ETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance	3			1.92	°C/W
$R_{\theta JA}$ Junction to free air thermal resistance				62.5	°C/W

resistive-load-switching characteristics at 25°C case temperature

	PARAMETER		TEST CONDITIONS †		MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = 3 A	I _{B(on)} = 12 mA	$I_{B(off)} = -12 \text{ mA}$		1.5		μs
t _{off}	Turn-off time	$V_{BE(off)} = -5 \text{ V}$	$R_L = 10 \Omega$	$t_p = 20 \ \mu s, \ dc \le 2\%$		8.5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

^{6.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.

TYPICAL CHARACTERISTICS

TYPICAL DC CURRENT GAIN COLLECTOR CURRENT TCS120AA 40000 = -40°C T_c = 25°C = 100°C h_{FE} - Typical DC Current Gain 10000 1000 3 V = 300 μ s, duty cycle < 2% 100 5.0 0.5 1.0 I_c - Collector Current - A

Figure 1.

COLLECTOR-EMITTER SATURATION VOLTAGE

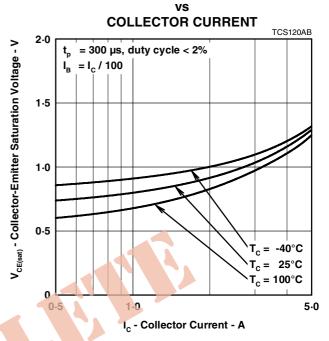
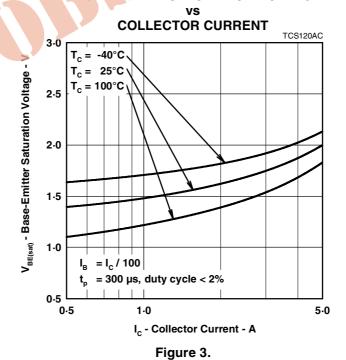


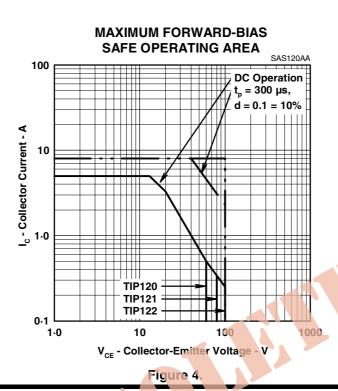
Figure 2.

BASE-EMITTER SATURATION VOLTAGE



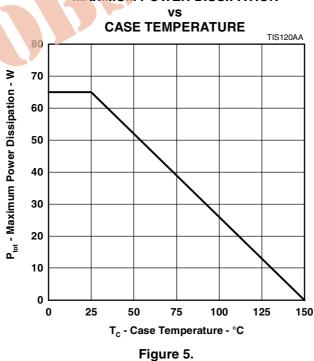
PRODUCT INFORMATION

MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

MAXIMUM POWER DISSIPATION



PRODUCT INFORMATION